

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI FMB150** is a high power transistor designed for FM broadcast system in 88-108 MHz range. It has diffused ballasting resistor to improve MTBF and high VSWR capability.

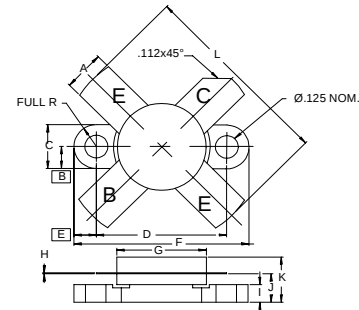
FEATURES:

- Class C, CE mode 28 V Operation
- $P_G = 9.0$ dB at 150 W/108 MHz
- **Omnigold™** Metalization System
- High VSWR capability

MAXIMUM RATINGS

I_C	16 A
V_{CBO}	55 V
V_{EBO}	4.0 V
P_{DISS}	165 W @ $T_C = 25^\circ C$
T_J	$-65^\circ C$ to $+200^\circ C$
T_{STG}	$-65^\circ C$ to $+150^\circ C$
θ_{JC}	$1.06^\circ C/W$

PACKAGE STYLE .500 4L FLG



DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.220 / 5.59	.230 / 5.84
B	.125 / 3.18	
C	.245 / 6.22	.255 / 6.48
D	.720 / 18.28	.730 / 18.54
E	.125 / 3.18	
F	.970 / 24.64	.980 / 24.89
G	.495 / 12.57	.505 / 12.83
H	.003 / 0.08	.007 / 0.18
I	.090 / 2.29	.110 / 2.79
J	.150 / 3.81	.175 / 4.45
K		.280 / 7.11
L	.980 / 24.89	1.050 / 26.67

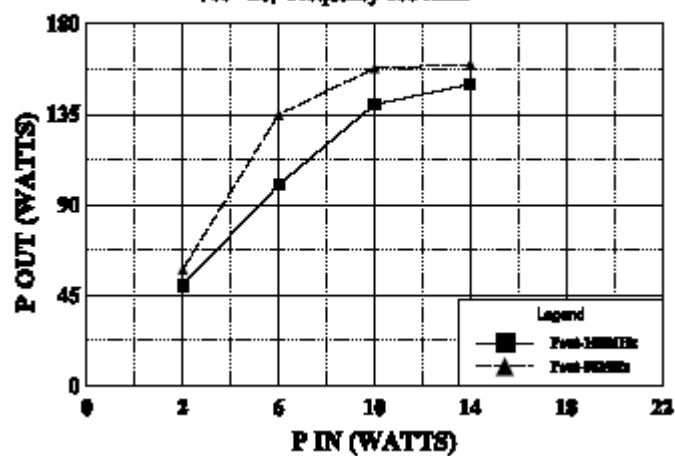
ORDER CODE: ASI10588

CHARACTERISTICS $T_C = 25^\circ C$

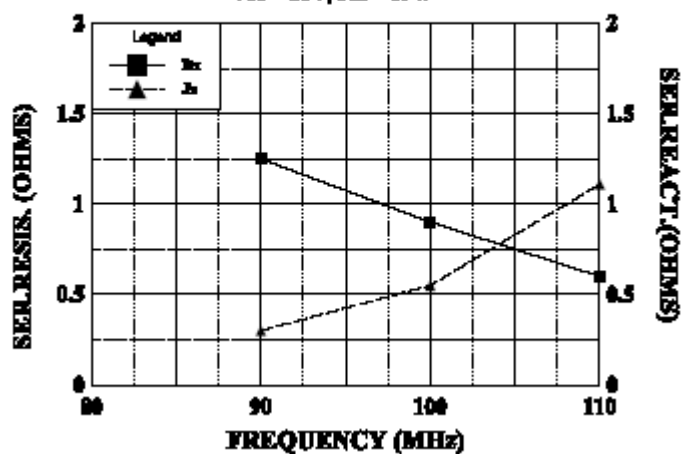
SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CBO}	$I_C = 100$ mA	55			V
BV_{CEO}	$I_C = 100$ mA	25			V
BV_{EBO}	$I_E = 20$ mA	4.0			V
h_{FE}	$V_{CE} = 5.0$ V $I_C = 1.0$ A	20			---
C_{OB}	$V_{CB} = 28$ V $f = 1.0$ MHz		140		pF
P_G	$V_{CC} = 28$ V $P_{OUT} = 150$ W $f = 108$ MHz	9.0	10		dB
η_C			65		%
VSWR				3:1	---

POWER OUTPUT vs POWER INPUT

$V_{CC} = 28V$, Frequency 108 MHz


SERIES INPUT IMPEDANCE vs FREQUENCY

$V_{CC} = 28V$, Pin = 19W


SERIES LOAD IMPEDANCE vs FREQUENCY

$V_{CC} = 28V$, Pin = 19W

